

2811

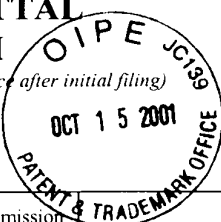
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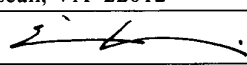
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<b>TRANSMITTAL FORM</b> (to be used for all correspondence after initial filing) 	<b>Application Number</b>	09/433,705
	<b>Filing Date</b>	November 4, 1999
	<b>First Named Inventor</b>	Shunpei YAMAZAKI
	<b>Group Art Unit</b>	2811
	<b>Examiner Name</b>	S. Loke
<b>Total Number of Pages in This Submission</b>	<b>Attorney Docket Number</b>	0756-2062

ENCLOSURES (check all that apply)		
<input type="checkbox"/> Fee Transmittal Form <input type="checkbox"/> Fee Attached <input checked="" type="checkbox"/> Amendment / Reply <input type="checkbox"/> After Final <input type="checkbox"/> Affidavits/declaration(s) <input type="checkbox"/> Extension of Time Request <input type="checkbox"/> Express Abandonment Request <input checked="" type="checkbox"/> Information Disclosure Statement and Notification of Related Application <input type="checkbox"/> Certified Copy of Priority Document(s) <input type="checkbox"/> Response to Missing Parts/Incomplete Application <input type="checkbox"/> Response to Missing Parts under 37 CFR 1.52 or 1.53	<input type="checkbox"/> Assignment Papers (for an Application) <input type="checkbox"/> Drawing(s) <input type="checkbox"/> Licensing-related Papers <input type="checkbox"/> Petition <input type="checkbox"/> Petition to Convert to a Provisional Application <input type="checkbox"/> Power of Attorney, Revocation Change of Correspondence Address <input type="checkbox"/> Terminal Disclaimer <input type="checkbox"/> Request for Refund <input type="checkbox"/> CD, Number of CD(s) _____	<input type="checkbox"/> After Allowance Communication to Group <input type="checkbox"/> Other
<b>Remarks</b>		<input checked="" type="checkbox"/> The Commissioner is hereby authorized to charge any additional fees required or credit any overpayments to Deposit Account No. 19-2380 for the above identified docket number.

SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT	
Firm or Individual name	Eric J. Robinson, Reg. No. 38,285 Nixon Peabody LLP 8180 Greensboro Drive Suite 800 McLean, VA 22012
Signature	
Date	October 15, 2001

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of )  
Shunpei YAMAZAKI ) Group Art Unit: 2811  
Serial No. 09/433,705 ) Examiner: S. Loke  
Filed: November 4, 1999 )  
For: METHOD OF FABRICATING )  
A SEMICONDUCTOR DEVICE )

#15/B  
11-13-01  
Payton

**AMENDMENT AND RESPONSE TO NON-COMPLIANT AMENDMENT**

Honorable Commissioner for Patents

Washington, D.C. 20231

Sir:

In response to the *Notice of Non-Compliant Amendment* of September 13, 2001, please amend the subject application as follows:

**IN THE CLAIMS:**

Please amend claim 13.

13. (Amended) A semiconductor device comprising:  
a first thin film transistor comprising:  
a semiconductor island on an insulating surface;  
a channel region in the semiconductor island;  
at least an LDD region being in contact with the channel region and including a first impurity region and a second impurity region, said first impurity region being in contact with the channel region and said second impurity region being in contact with the first impurity region;  
at least a third impurity region being in contact with the second impurity region; a gate electrode being formed over the semiconductor island with a gate insulating film interposed therebetween and having a first gate electrode and a second electrode being formed on the first gate electrode,  
wherein the first gate electrode has at least a taper portion and a flat portion,  
wherein the first impurity region is overlapped with the taper portion of the first gate electrode with the gate insulating film interposed therebetween,